

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (canceled)
2. (canceled)
3. (canceled)
4. (canceled)
5. (canceled)
6. (canceled)
7. (canceled)
8. (canceled)
9. (canceled)
10. (canceled)

11. (previously presented) A semiconductor integrated circuit device comprising:  
trenches formed in a semiconductor substrate and defining active regions and dummy regions; and  
element isolation insulating films buried in said trenches such that said element isolation insulating films serve as element isolation regions,  
wherein said dummy regions are formed at a scribing area.

12. (previously presented) A semiconductor integrated circuit device according to claim 11, wherein a length of said dummy region is shorter than a distance between external terminals.

13. (previously presented) A semiconductor integrated circuit device comprising:

trenches formed in a semiconductor substrate and defining active regions and dummy regions; and

insulating films buried in said trenches such that said insulating films serve as element isolation insulating films;

wherein said dummy regions are formed at a scribing area.

14. (previously presented) A semiconductor integrated circuit device according to claim 13, wherein a length of said dummy region is shorter than a distance between bonding pads.

15. (previously presented) A semiconductor integrated circuit device comprising:

trenches formed in a semiconductor substrate and defining active regions and dummy regions; and

element isolation insulating films buried in said trenches,

wherein said dummy regions are formed at a scribing area.

16. (previously presented) A semiconductor integrated circuit device according to claim 15, wherein a length of said dummy region is shorter than a distance between external terminals.